

N-channel TrenchMOS intermediate level FET

Rev. 1 — 18 August 2010

Product data sheet

1. Product profile

1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Suitable for intermediate level gate drive sources

1.3 Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control

1.4 Quick reference data

Table 1. Quick reference data

- Suitable for thermally demanding environments due to 175 °C rating
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

Parameter	Conditions		Min	Тур	Max	Unit
drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V
drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u>	[1]	-	-	120	A
total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	306	W
racteristics						
drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 11</u>		-	1.6	1.9	mΩ
	Parameter drain-source voltage drain current total power dissipation tracteristics drain-source on-state	$\begin{array}{ll} \mbox{drain-source} & T_j \geq 25 \ {}^\circ\mbox{C}; \ T_j \leq 175 \ {}^\circ\mbox{C} \\ \mbox{oltage} & \mbox{drain current} & V_{GS} = 10 \ V; \ T_{mb} = 25 \ {}^\circ\mbox{C}; \\ \mbox{see} \ \hline \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ $	$\begin{tabular}{ c c c c } \hline Parameter & Conditions \\ \hline drain-source & T_j \ge 25 \ ^\circ C; \ T_j \le 175 \ ^\circ C \\ \hline voltage & & & \\ \hline drain \ current & V_{GS} = 10 \ V; \ T_{mb} = 25 \ ^\circ C; & & \\ \hline see \ Figure \ 1 & & \\ \hline total \ power & & \\ \hline drain \ source & & \\ \hline mathbf{aracteristics} & & \\ \hline drain-source & & V_{GS} = 10 \ V; \ I_D = 25 \ A; \\ \hline on-state & & T_j = 25 \ ^\circ C; \ see \ Figure \ 11 & \\ \hline \end{array}$	$\begin{tabular}{ c c c c } \hline Parameter & Conditions & Min \\ \hline drain-source & T_j \ge 25 \ ^\circ C; \ T_j \le 175 \ ^\circ C & - \\ \hline voltage & & & \\ \hline drain \ current & V_{GS} = 10 \ V; \ T_{mb} = 25 \ ^\circ C; & & \\ \hline see \ \hline Figure \ 1 & & \\ \hline total \ power & & \\ \hline drain \ source & T_{mb} = 25 \ ^\circ C; \ see \ \hline Figure \ 2 & - \\ \hline ext{and} \ racteristics & & \\ \hline drain-source & V_{GS} = 10 \ V; \ I_D = 25 \ A; & - \\ \hline on-state & & T_j = 25 \ ^\circ C; \ see \ \hline Figure \ 11 & & \\ \hline ext{and} \ Figure \ 11 & & \\ \hline ext{and} $	ParameterConditionsMinTypdrain-source voltage $T_j \ge 25 \ ^{\circ}C; T_j \le 175 \ ^{\circ}C$ drain current $V_{GS} = 10 \ V; T_{mb} = 25 \ ^{\circ}C;$ [1]drain current $V_{GS} = 10 \ V; T_{mb} = 25 \ ^{\circ}C;$ see Figure 1total power dissipation $T_{mb} = 25 \ ^{\circ}C;$ see Figure 2tracteristicsdrain-source on-state $V_{GS} = 10 \ V; \ I_D = 25 \ A;$ $T_j = 25 \ ^{\circ}C;$ see Figure 11-1.6	ParameterConditionsMinTypMaxdrain-source voltage $T_j \ge 25 \ ^\circ\text{C}; \ T_j \le 175 \ ^\circ\text{C}$ 40drain current $V_{GS} = 10 \ V; \ T_{mb} = 25 \ ^\circ\text{C};$ [1]120drain current $V_{GS} = 10 \ V; \ T_{mb} = 25 \ ^\circ\text{C};$ [1]306total power dissipation $T_{mb} = 25 \ ^\circ\text{C};$ see Figure 2306tracteristicsdrain-source on-state $V_{GS} = 10 \ V; \ I_D = 25 \ A;$ $T_j = 25 \ ^\circ\text{C};$ see Figure 11-1.61.9



N-channel TrenchMOS intermediate level FET

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 120 \text{ A}; \text{V}_{sup} \leq 40 \text{ V}; \\ R_{GS} &= 50 \Omega; \text{V}_{GS} = 10 \text{ V}; \\ T_{j(\text{init})} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $	-	-	1.02	J
Dynamic of	characteristics					
Q _{GD}	gate-drain charge	$\begin{split} I_D &= 25 \text{ A}; V_{DS} = 32 \text{ V}; \\ V_{GS} &= 10 \text{ V}; \text{ see } \underline{Figure \ 13}; \\ \text{see } \underline{Figure \ 14} \end{split}$	-	72	-	nC

[1] Continuous current is limited by package.

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	Drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

3. Ordering information

Table 3. Ordering	information		
Type number	Package		
	Name	Description	Version
BUK661R9-40C	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

Rev. 1 — 18 August 2010

N-channel TrenchMOS intermediate level FET

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	40	V
V _{GS}	gate-source voltage	Pulsed	<u>[1]</u>	-20	20	V
		DC	[2]	-16	16	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{10000000000000000000000000000000000$	[3]	-	120	А
		T_{mb} = 100 °C; V_{GS} = 10 V; see Figure 1	[3]	-	120	А
I _{DM}	peak drain current	$T_{mb} = 25 \text{ °C}; t_p \le 10 \mu\text{s}; \text{ pulsed};$ see Figure 3		-	1107	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	306	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	in diode					
ls	source current	T _{mb} = 25 °C	[3]	-	120	А
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	1107	А
Avalanche r	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:ld} \begin{array}{l} I_{D} = 120 \; A; \; V_{sup} \leq 40 \; V; \; R_{GS} = 50 \; \Omega; \\ V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; unclamped \end{array}$		-	1.02	J
E _{DS(AL)R}	repetitive drain-source avalanche energy		<u>[4][5][6]</u>	-	-	J

[1] Accumulated pulse duration not to exceed 5mins.

[2] -16V accumulated duration not to exceed 168 hrs

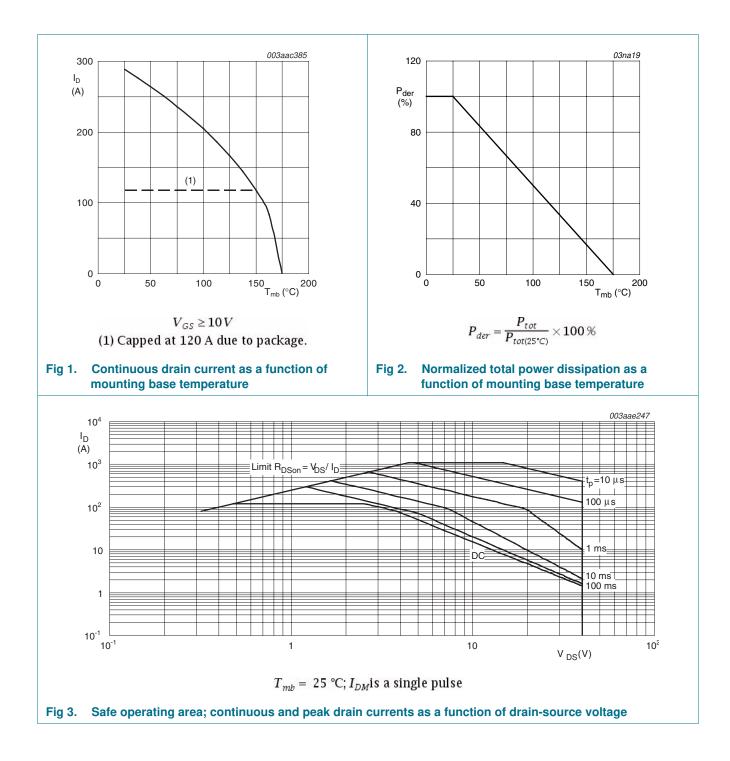
[3] Continuous current is limited by package.

[4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[5] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

[6] Refer to application note AN10273 for further information.

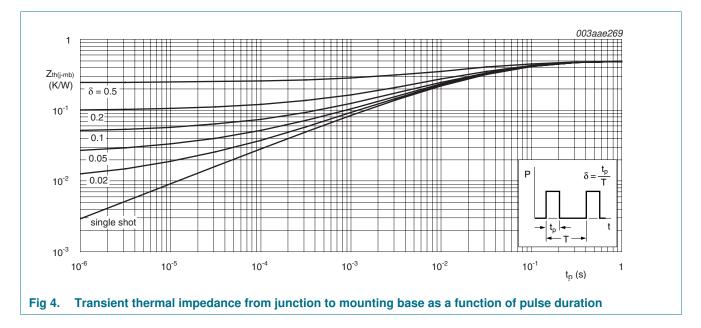
BUK661R9-40C



N-channel TrenchMOS intermediate level FET

Thermal characteristics 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.49	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W



N-channel TrenchMOS intermediate level FET

6. Characteristics

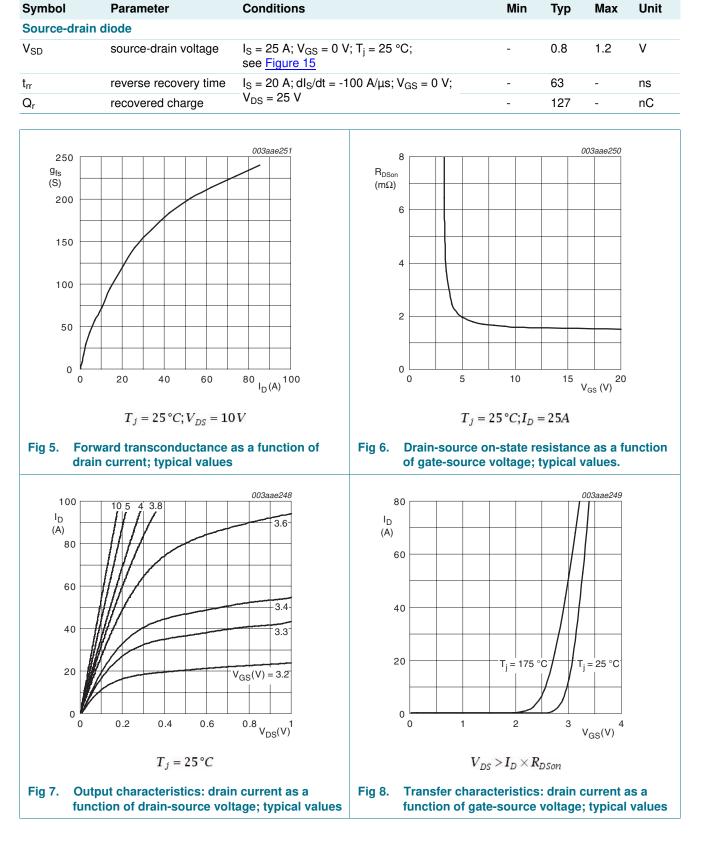
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = 25 \ ^{\circ}C$	40	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	36	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	1.8	2.3	2.8	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 10</u>	-	-	3.3	V
		I _D = 2.5 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 10</u>	0.8	-	-	V
DSS drain leakage current		V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
I _{GSS}	gate leakage current	$V_{DS} = 0 V; V_{GS} = 20 V; T_j = 25 \ ^{\circ}C$	-	2	100	nA
		$V_{DS} = 0 V; V_{GS} = -20 V; T_j = 25 \ ^{\circ}C$	-	2	100	nA
	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u>	-	1.6	1.9	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u>	-	2	2.6	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u>	-	2.25	3.1	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 11</u>	-	-	4	mΩ
Dynamic ch	aracteristics					
$Q_{G(tot)}$ total gate charge		$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 13</u> ; see <u>Figure 14</u>	-	260	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 5 \text{ V};$ see <u>Figure 13</u> ; see <u>Figure 14</u>	-	147	-	nC
Q _{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$	-	38	-	nC
Q _{GD}	gate-drain charge	see <u>Figure 13;</u> see <u>Figure 14</u>	-	72	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	11.3	15.1	nF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{16}$	-	1447	1750	pF
C _{rss}	reverse transfer capacitance		-	1014	1390	pF
d(on)	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	60	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega$	-	140	-	ns
d(off)	turn-off delay time		-	234	-	ns
ⁱ f	fall time		-	416	-	ns
LD	internal drain inductance	from upper edge of drain mounting base to centre of die; $T_j = 25 \text{ °C}$	-	3.5	-	nH
L _S	internal source inductance	from source lead to source bond pad; T _j = 25 °C	-	7.5	-	nH

Table 6.

Characteristics ... continued

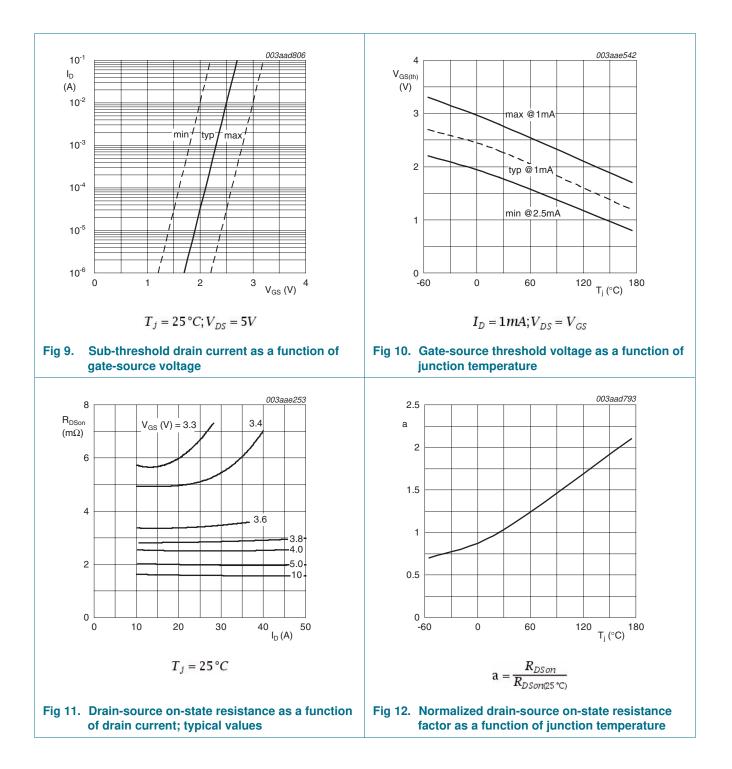
BUK661R9-40C

N-channel TrenchMOS intermediate level FET

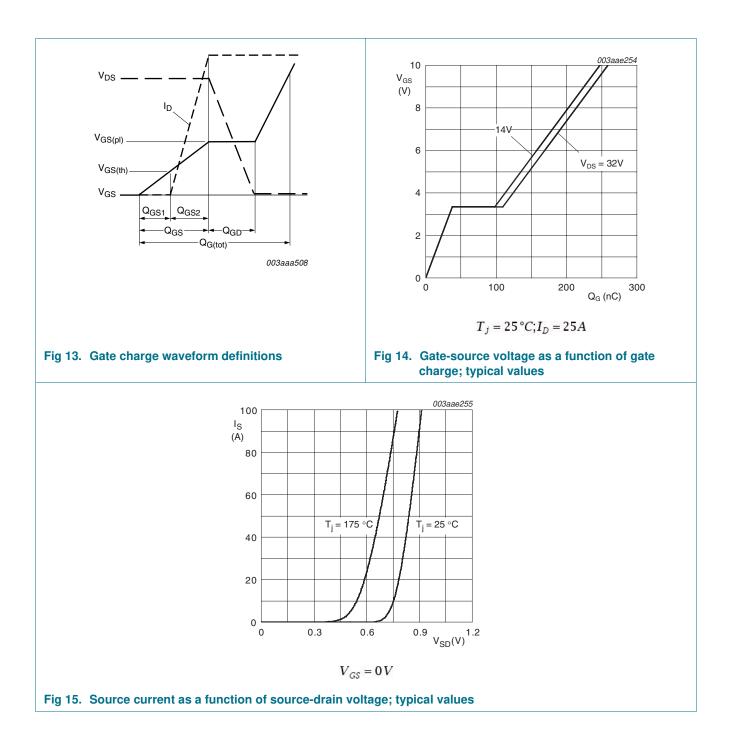


BUK661R9-40C

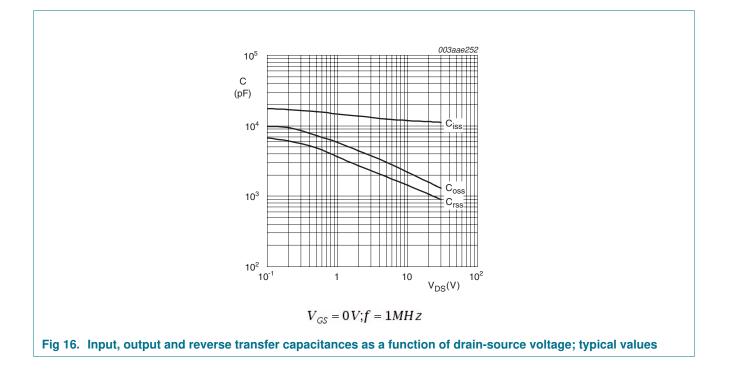
BUK661R9-40C



BUK661R9-40C



BUK661R9-40C



N-channel TrenchMOS intermediate level FET

7. Package outline

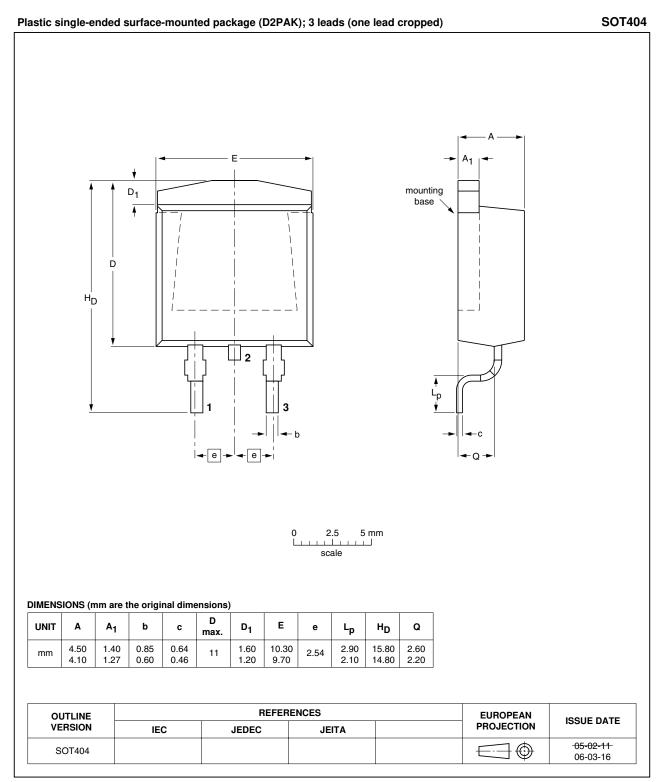


Fig 17. Package outline SOT404 (D2PAK)

All information provided in this document is subject to legal disclaimers.

BUK661R9-40C

N-channel TrenchMOS intermediate level FET

8. Revision history

Table 7. Revision h	Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
BUK661R9-40C v.1	20100818	Product data sheet	-	-			

N-channel TrenchMOS intermediate level FET

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nexperia</u>.com.

9.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Nexperia does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Nexperia sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Nexperia and its customer, unless Nexperia and

customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Nexperia product is deemed to offer functions and qualities beyond those described in the Product data sheet.

9.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Nexperia does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

In no event shall Nexperia be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Nexperia's aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of Nexperia.

Right to make changes — Nexperia reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use in automotive applications — This Nexperia product has been qualified for use in automotive

applications. The product is not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of a Nexperia product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Nexperia accepts no liability for inclusion and/or use of Nexperia products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. Nexperia makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using Nexperia products, and Nexperia accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the Nexperia product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

Nexperia does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using Nexperia products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). Nexperia does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale - Nexperia

products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nexperia.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual

Product data sheet

N-channel TrenchMOS intermediate level FET

agreement is concluded only the terms and conditions of the respective agreement shall apply. Nexperia hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Nexperia products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

10. Contact information

For more information, please visit: http://www.nexperia.com

For sales office addresses, please send an email to: <u>salesaddresses@nexperia.com</u>

9.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

N-channel TrenchMOS intermediate level FET

11. Contents

1	Product profile1
1.1	General description1
1.2	Features and benefits
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values3
5	Thermal characteristics5
6	Characteristics6
7	Package outline11
8	Revision history12
9	Legal information13
9.1	Data sheet status13
9.2	Definitions
9.3	Disclaimers
9.4	Trademarks14
10	Contact information14